



#### Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	$I_D$
20V	48mΩ@4.5V	3A
	55mΩ@2.5V	
	69mΩ@2.5V	

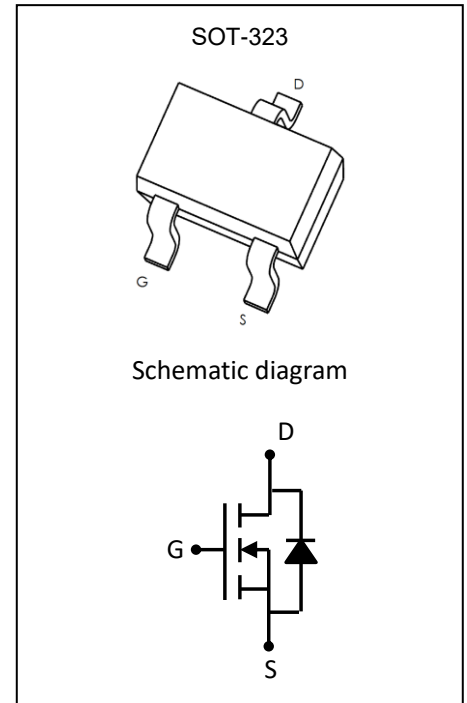
#### Feature

- TrenchFET Power MOSFET
- Excellent  $R_{DS(on)}$  and Low Gate Charge

#### Application

- DC/DC Converter
- Load Switch for Portable Devices
- Battery Switch

#### MARKING:



#### ABSOLUTE MAXIMUM RATINGS ( $T_a=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	$V_{DS}$	20	V
Gate-Source Voltage	$V_{GS}$	$\pm 12$	V
Continuous Drain Current	$I_D$	3	A
Pulsed Drain Current ( $t=300\mu\text{s}$ )	$I_{DM}$	9	A
Power Dissipation	$P_D$	0.2	W
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	625	$^\circ\text{C/W}$
Junction Temperature	$T_J$	150	$^\circ\text{C}$
Storage Temperature	$T_{STG}$	-55~ +150	$^\circ\text{C}$

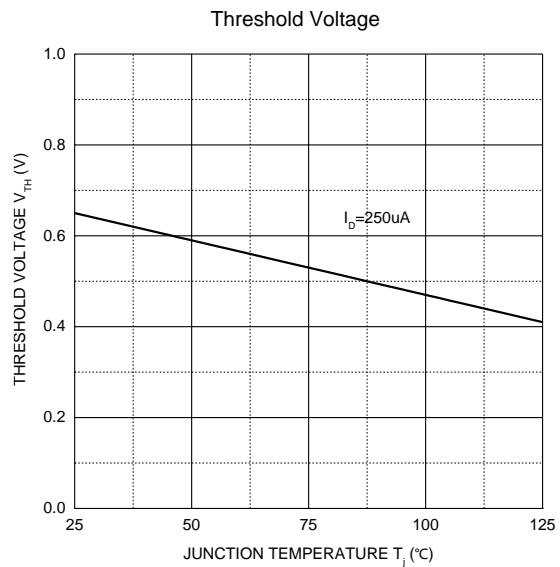
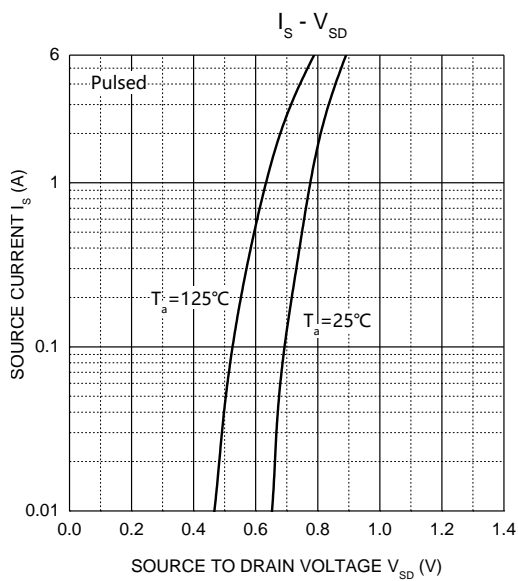
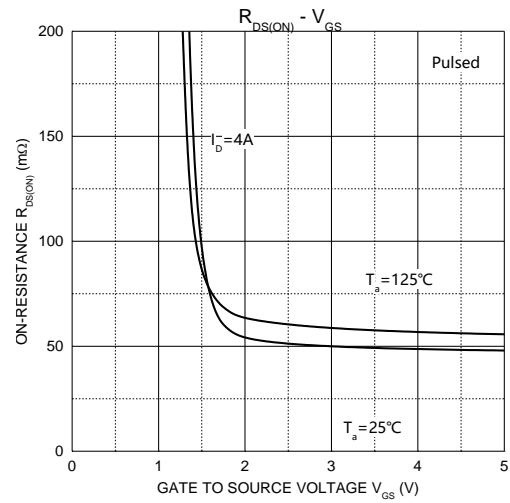
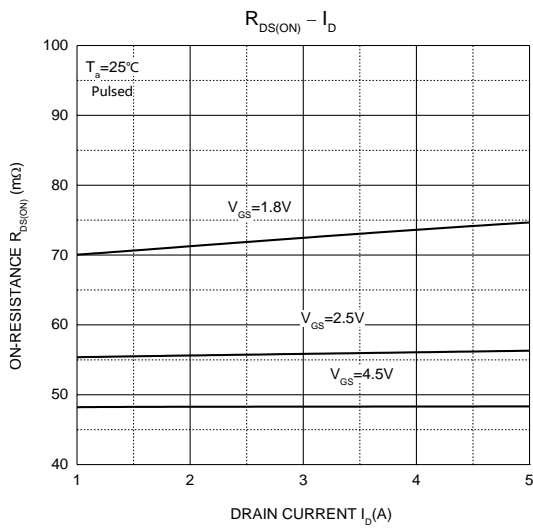
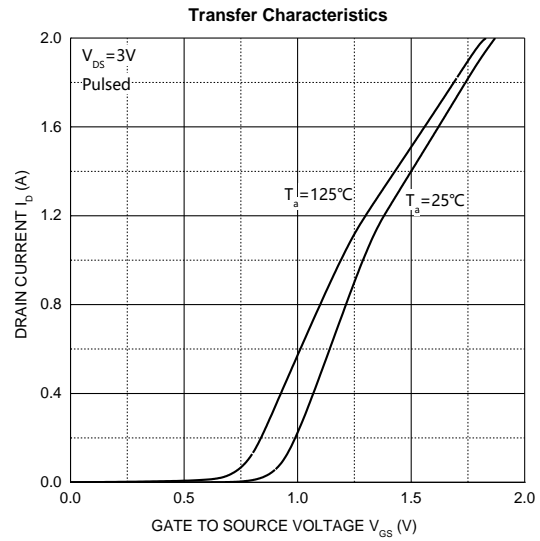
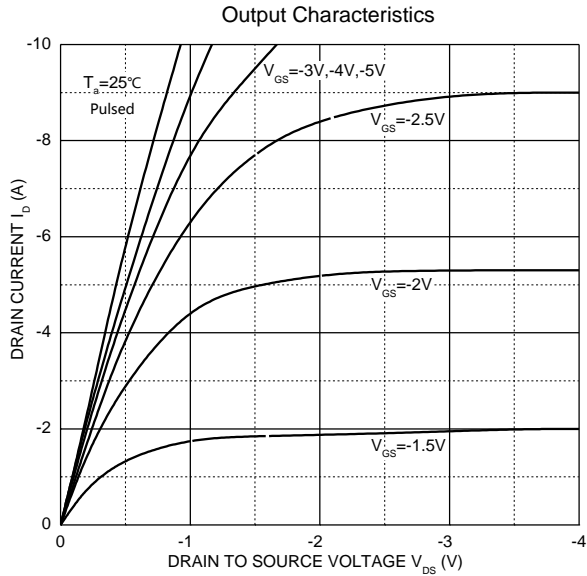
**MOSFET ELECTRICAL CHARACTERISTICS(T<sub>a</sub>=25°C unless otherwise noted)**

Parameter	Symbol	Test Condition	Min	Type	Max	Unit
<b>Static Characteristics</b>						
Drain-source breakdown voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> = 0V, I <sub>D</sub> =250μA	20			V
Zero gate voltage drain current	I <sub>DSS</sub>	V <sub>DS</sub> =16V, V <sub>GS</sub> = 0V			1	μA
Gate-body leakage current	I <sub>GSS</sub>	V <sub>GS</sub> =±12V, V <sub>DS</sub> = 0V			±0.1	μA
Gate threshold voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA	0.4	0.6	1.0	V
Drain-source on-resistance <sup>1</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> =4.5V, I <sub>D</sub> =4A		48	63	mΩ
		V <sub>GS</sub> =2.5V, I <sub>D</sub> =2.5A		55	72	
		V <sub>GS</sub> =1.8V, I <sub>D</sub> =1.5A		69	89	
Forward tranconductance <sup>1</sup>	g <sub>FS</sub>	V <sub>DS</sub> =5V, I <sub>D</sub> =4A	10			S
<b>Dynamic characteristics</b>						
Input Capacitance <sup>2</sup>	C <sub>iss</sub>	V <sub>DS</sub> =10V, V <sub>GS</sub> =0V, f=1MHz		480		pF
Output Capacitance <sup>2</sup>	C <sub>oss</sub>			85		
Reverse Transfer Capacitance <sup>2</sup>	C <sub>rss</sub>			65		
Total gate charge	Q <sub>g</sub>	V <sub>DS</sub> =10V, V <sub>GS</sub> =4.5V, I <sub>D</sub> =4A		6.8		nC
Gate-source charge	Q <sub>gs</sub>			1.1		
Gate-drain charge	Q <sub>gd</sub>			2.8		
<b>Switching Characteristics<sup>2</sup></b>						
Turn-on delay time	t <sub>d(on)</sub>	V <sub>DD</sub> =10V, R <sub>L</sub> =5.5Ω, I <sub>D</sub> =4A V <sub>GEN</sub> =4.5V, R <sub>g</sub> =6Ω		12		ns
Turn-on rise time	t <sub>r</sub>			80		
Turn-off delay time	t <sub>d(off)</sub>			26		
Turn-off fall time	t <sub>f</sub>			13		
<b>Source-Drain Diode characteristics</b>						
Diode Forward voltage	V <sub>DS</sub>	V <sub>GS</sub> =0V, I <sub>S</sub> =1A		0.7	1.2	V

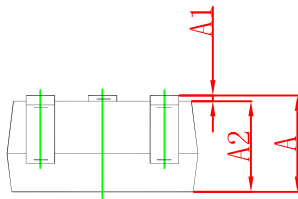
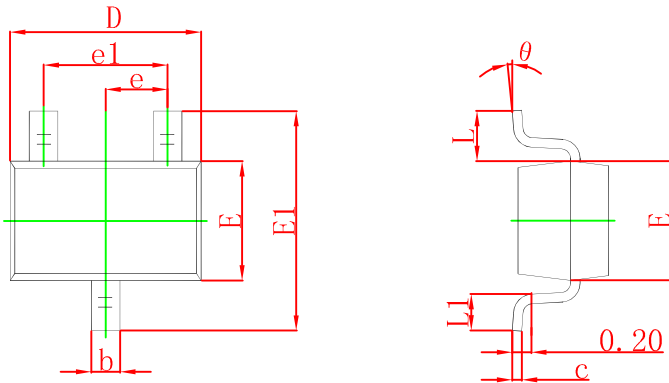
**Notes:**

1. Pulse test; pulse width≤300μs, duty cycle≤2%.
2. Guaranteed by design, not subject to production testing.

**Typical Electrical and Thermal Characteristics**



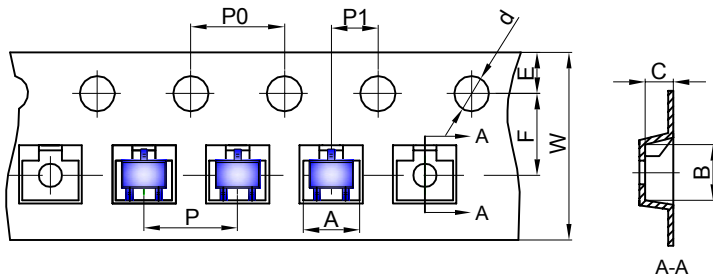
## SOT-323 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.100	0.035	0.043
A1	0.000	0.100	0.000	0.004
A2	0.900	1.000	0.035	0.039
b	0.200	0.400	0.008	0.016
c	0.080	0.150	0.003	0.006
D	2.000	2.200	0.079	0.087
E	1.150	1.350	0.045	0.053
E1	2.150	2.450	0.085	0.096
e	0.650 TYP		0.026 TYP	
e1	1.200	1.400	0.047	0.055
L	0.525 REF		0.021 REF	
L1	0.260	0.460	0.010	0.018
$\theta$	0°	8°	0°	8°

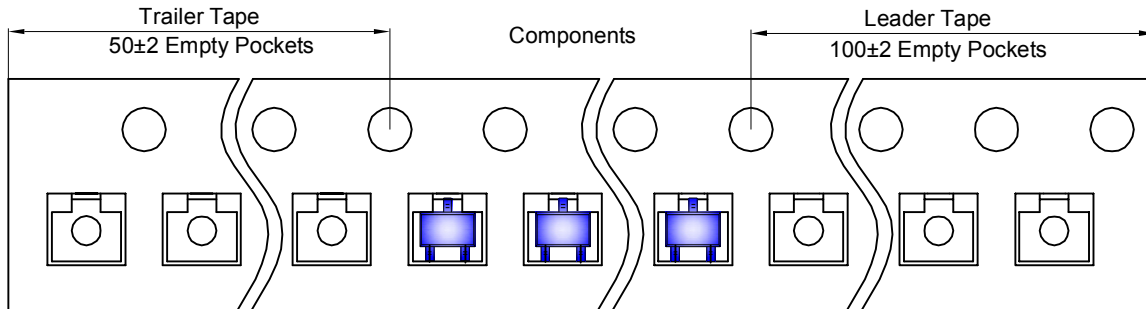
## SOT-323 Tape and Reel

### SOT-323 Embossed Carrier Tape

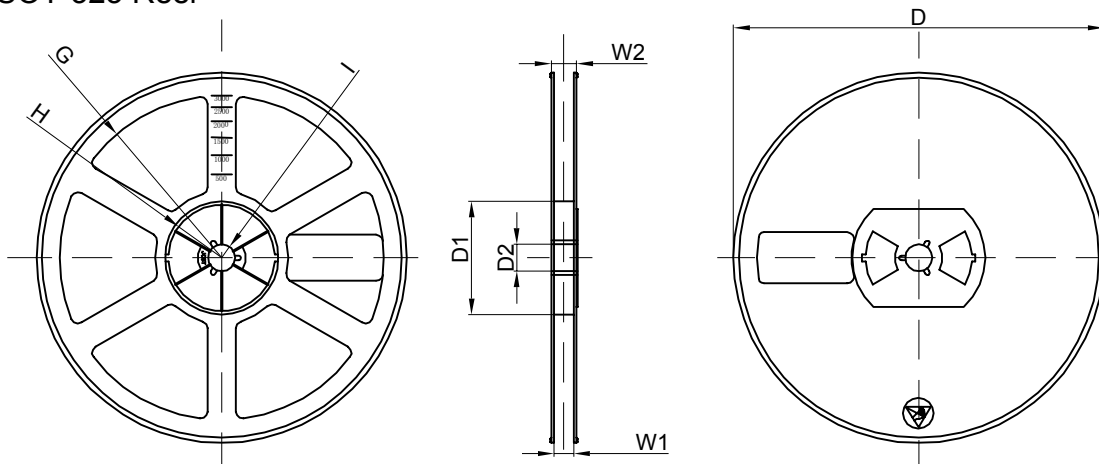


Dimensions are in millimeter										
Pkg type	A	B	C	d	E	F	P0	P	P1	W
SOT-323	2.25	2.55	1.19	Ø1.55	1.75	3.50	4.00	4.00	2.00	8.00

### SOT-323 Tape Leader and Trailer



### SOT-323 Reel



Dimensions are in millimeter								
Reel Option	D	D1	D2	G	H	I	W1	W2
7" Dia	Ø178.00	54.40	13.00	R78.00	R25.60	R6.50	9.50	12.30

REEL	Reel Size	Box	Box Size(mm)	Carton	Carton Size(mm)	G.W.(kg)
3000 pcs	7 inch	30,000 pcs	203×203×195	120,000 pcs	438×438×220	